

# Kwang-Sik Jeong

## List of Publications by Year in descending order

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47  
papers

671  
citations

516710

16  
h-index

642732

23  
g-index

47  
all docs

47  
docs citations

47  
times ranked

1006  
citing authors

#	ARTICLE	IF	CITATIONS
1	Interaction- and defect-free van der Waals contacts between metals and two-dimensional semiconductors. <i>Nature Electronics</i> , 2022, 5, 241-247.	26.0	84
2	Thermal and Electrical Conduction of Single-crystal Bi <sub>2</sub> Te <sub>3</sub> Nanostructures grown using a one step process. <i>Scientific Reports</i> , 2016, 6, 19132.	3.3	45
3	Structural Evolution and the Control of Defects in Atomic Layer Deposited HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Stacked Films on GaAs. <i>ACS Applied Materials &amp; Interfaces</i> , 2013, 5, 1982-1989.	8.0	34
4	Evolution of crystal structures in GeTe during phase transition. <i>Scientific Reports</i> , 2017, 7, 955.	3.3	32
5	Reversible Fermi Level Tuning of a Sb <sub>2</sub> Te <sub>3</sub> Topological Insulator by Structural Deformation. <i>Nano Letters</i> , 2015, 15, 3820-3826.	9.1	31
6	Controlling the defects and transition layer in SiO <sub>2</sub> films grown on 4H-SiC via direct plasma-assisted oxidation. <i>Scientific Reports</i> , 2016, 6, 34945.	3.3	29
7	Effect of the Thermal Conductivity on Resistive Switching in GeTe and Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Nanowires. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 21819-21827.	8.0	25
8	Tuning the Fermi level with topological phase transition by internal strain in a topological insulator Bi <sub>2</sub> Se <sub>3</sub> thin film. <i>Nanoscale</i> , 2016, 8, 741-751.	5.6	23
9	p-n Junction Diode Using Plasma Boron-Doped Black Phosphorus for High-Performance Photovoltaic Devices. <i>ACS Nano</i> , 2019, 13, 1683-1693.	14.6	23
10	Ultrafast phase change and long durability of BN-incorporated GeSbTe. <i>Journal of Materials Chemistry C</i> , 2015, 3, 1707-1715.	5.5	21
11	Modulation of phase change characteristics in Ag-incorporated Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> owing to changes in structural distortion and bond strength. <i>Journal of Materials Chemistry C</i> , 2017, 5, 3973-3982.	5.5	20
12	Closing the Surface Bandgap in Thin Bi <sub>2</sub> Se <sub>3</sub> /Graphene Heterostructures. <i>ACS Nano</i> , 2019, 13, 3931-3939.	14.6	20
13	Filament Geometry Induced Bipolar, Complementary and Unipolar Resistive Switching under the Same Set Current Compliance in Pt/SiO <sub>x</sub> /TiN. <i>Scientific Reports</i> , 2015, 5, 15374.	3.3	18
14	Electric field effect dominated bipolar resistive switching through interface control in a Pt/TiO <sub>2</sub> /TiN structure. <i>RSC Advances</i> , 2015, 5, 221-230.	3.6	18
15	Structural and Electrical Properties of EOT HfO <sub>2</sub> (<1 nm) Grown on InAs by Atomic Layer Deposition and Its Thermal Stability. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 7489-7498.	8.0	18
16	Electrical properties and thermal stability in stack structure of HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> /InSb by atomic layer deposition. <i>Scientific Reports</i> , 2017, 7, 11337.	3.3	17
17	Characterization of Rotational Stacking Layers in Large-Area MoSe <sub>2</sub> Film Grown by Molecular Beam Epitaxy and Interaction with Photon. <i>ACS Applied Materials &amp; Interfaces</i> , 2017, 9, 30786-30796.	8.0	16
18	Effects of Nitrogen Incorporation in HfO <sub>2</sub> Grown on InP by Atomic Layer Deposition: An Evolution in Structural, Chemical, and Electrical Characteristics. <i>ACS Applied Materials &amp; Interfaces</i> , 2014, 6, 3896-3906.	8.0	15

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19	Ultrafast photocarrier dynamics related to defect states of Si <sub>1-x</sub> Ge <sub>x</sub> nanowires measured by optical pump-probe spectroscopy. <i>Nanoscale</i> , 2017, 9, 8015-8023.	5.6	13
20	Improving Electrical Properties by Effective Sulfur Passivation via Modifying the Surface State of Substrate in HfO <sub>2</sub> /InP Systems. <i>Journal of Physical Chemistry C</i> , 2018, 122, 7226-7235.	3.1	13
21	Enhanced Photoinduced Carrier Generation Efficiency through Surface Band Bending in Topological Insulator Bi <sub>2</sub> Se <sub>3</sub> Thin Films by the Oxidized Layer. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 26649-26658.	8.0	12
22	Ultrafast Photoresponse by Surface State-Mediated Optical Transitions in Topological Insulator Bi <sub>2</sub> Te <sub>3</sub> Nanowire. <i>Advanced Optical Materials</i> , 2019, 7, 1900621.	7.3	11
23	Enhanced Spin-to-Charge Conversion Efficiency in Ultrathin Bi <sub>2</sub> Se <sub>3</sub> Observed by Spintronic Terahertz Spectroscopy. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 23153-23160.	8.0	11
24	Modulation of optoelectronic properties of the Bi <sub>2</sub> Te <sub>3</sub> nanowire by controlling the formation of selective surface oxidation. <i>Applied Surface Science</i> , 2021, 548, 149069.	6.1	10
25	Ferroelastic-Ferroelectric Multiferroicity in van der Waals Rhenium Dichalcogenides. <i>Advanced Materials</i> , 2022, 34, e2108777.	21.0	10
26	Disorder-induced decoupled surface transport channels in thin films of doped topological insulators. <i>Physical Review B</i> , 2018, 98, .	3.2	9
27	Trap-assisted high responsivity of a phototransistor using bi-layer MoSe <sub>2</sub> grown by molecular beam epitaxy. <i>Applied Surface Science</i> , 2019, 494, 37-45.	6.1	9
28	Effects of thermal and electrical stress on defect generation in InAs metal-oxide-semiconductor capacitor. <i>Applied Surface Science</i> , 2019, 467-468, 1161-1169.	6.1	8
29	Enhancement of photoresponse in Bi <sub>2</sub> Se <sub>3</sub> /graphene heterostructures by effective electron-hole separation through internal band bending. <i>Applied Surface Science</i> , 2021, 554, 149623.	6.1	8
30	Effects of spontaneous nitrogen incorporation by a 4H-SiC(0001) surface caused by plasma nitridation. <i>Journal of Materials Chemistry C</i> , 2015, 3, 5078-5088.	5.5	7
31	Effects of resonant bonding and structural distortion on the phase change properties of Sn <sub>2</sub> Sb <sub>2</sub> Se <sub>5</sub> . <i>Journal of Materials Chemistry C</i> , 2017, 5, 7820-7829.	5.5	7
32	Ferroelectric switching in GeTe through rotation of lone-pair electrons by Electric field-driven phase transition. <i>Applied Materials Today</i> , 2021, 24, 101122.	4.3	7
33	Ultrathin platinum diselenide synthesis controlling initial growth kinetics: Interfacial reaction depending on thickness and substrate. <i>Applied Surface Science</i> , 2021, 564, 150300.	6.1	7
34	Effect of substrate on photo-induced persistent photoconductivity in InAs nanowires. <i>Applied Surface Science</i> , 2018, 458, 964-971.	6.1	6
35	Quantitative analysis of defect states in amorphous InGaZnO thin-film transistors using photoinduced current transient spectroscopy. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	6
36	Structural deformation and void formation driven by phase transformation in the Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> film. <i>Journal of Materials Chemistry C</i> , 2014, 2, 2001.	5.5	5

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37	Topological Phase Control of Surface States in Bi <sub>2</sub> Se <sub>3</sub> via Spin-Orbit Coupling Modulation through Interface Engineering between HfO <sub>2</sub> . ACS Applied Materials & Interfaces, 2020, 12, 12215-12226.	8.0	4
38	Induction of the surface plasmon resonance from C-incorporated Au catalyst in Si <sub>1-x</sub> C <sub>x</sub> nanowires. Journal of Materials Chemistry, 2012, 22, 19744.	6.7	3
39	The effect of structural and chemical bonding changes on the optical properties of Si/Si <sub>1-x</sub> C <sub>x</sub> core/shell nanowires. Journal of Materials Chemistry C, 2013, 1, 5207.	5.5	3
40	Phase-change-induced martensitic deformation and slip system in GeSbTe. RSC Advances, 2015, 5, 35792-35800.	3.6	3
41	Optical characteristics of type-II hexagonal-shaped GaSb quantum dots on GaAs synthesized using nanowire self-growth mechanism from Ga metal droplet. Scientific Reports, 2021, 11, 7699.	3.3	3
42	Controlling resistive switching behavior in the solution processed SiO <sub>2-x</sub> device by the insertion of TiO <sub>2</sub> nanoparticles. Scientific Reports, 2022, 12, 8405.	3.3	3
43	Switching to Hidden Metallic Crystal Phase in Phase-Change Materials by Photoenhanced Metavalent Bonding. ACS Nano, 2022, , .	14.6	2
44	Phase Change <i>via</i> Intermediary Metastable Local Structure of Ge Atoms in Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Nanowires during Electrical Switching. ACS Applied Electronic Materials, 2020, 2, 2418-2428.	4.3	1
45	Quantification of point and line defects in Si <sub>0.6</sub> Ge <sub>0.4</sub> alloys with thickness variation via optical pump-THz probe measurement. Applied Surface Science, 2020, 513, 145815.	6.1	1
46	Terahertz spectroscopy of topological insulator Sb <sub>2</sub> Se <sub>3</sub> and its ultrafast nonequilibrium carrier dynamics. , 2016, , .		0
47	Oxidation Mechanism of Si <sub>1-x</sub> Ge <sub>x</sub> Nanowires with Au Catalyst Tip as a Function of Ge Content. ACS Applied Materials & Interfaces, 2017, 9, 37411-37418.	8.0	0